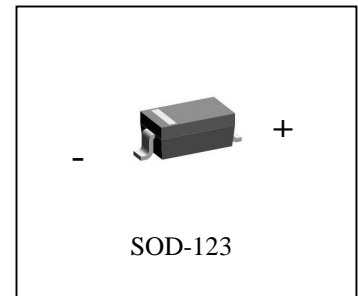


SCHOTTKY BARRIER DIODE
SD103AW/BW/CW
FEATURES

- Low Forward Voltage Drop.
- Guard Ring Construction For Transient Protection.
- Negligible Reverse Recovery Time.
- Low Reverse Capacitance.


MARKING: SD103AW :S4 SD103BW:S5 SD103CW:S6

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	SD103AW	SD103BW	SD103CW	Unit
Non-Repetitive Peak reverse voltage	V_{RM}	40	30	20	V
Peak Repetitive Peak reverse voltage	V_{RRM}				V
Working Peak Reverse Voltage	V_{RWM}				V
DC Blocking	V_R	28	21	14	V
Forward Continuous Current	I_F	350			mA
Repetitive Peak Forward Current @t 1.0s	I_{FRM}	1.5			A
Power Dissipation	P_d	400			mW
Thermal Resistance Junction to Ambient	R_{jA}	300			°C/W
Storage temperature	T_{stg}	-65-125			°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	$V_{(BR)R}$	40			V	$I_R=10\mu A$
		30			V	$I_R=10\mu A$
		20			V	$I_R=10\mu A$
Forward voltage	V_F			0.37 0.60	V	$I_F=20mA$ $I_F=200mA$
Reverse current	I_{RM}			5.0	μA	$V_R=30V$
				5.0	μA	$V_R=20V$
				5.0	μA	$V_R=10V$
Capacitance between terminals	C_T		50		pF	$V_R=0, f=1MHz$
Reverse Recovery Time	t_{rr}		10		ns	$I_R=I_F=200mA$ $I_{rr}=0.1*I_R, R_L=100$

SD103AW/BW/CW Typical Characteristics

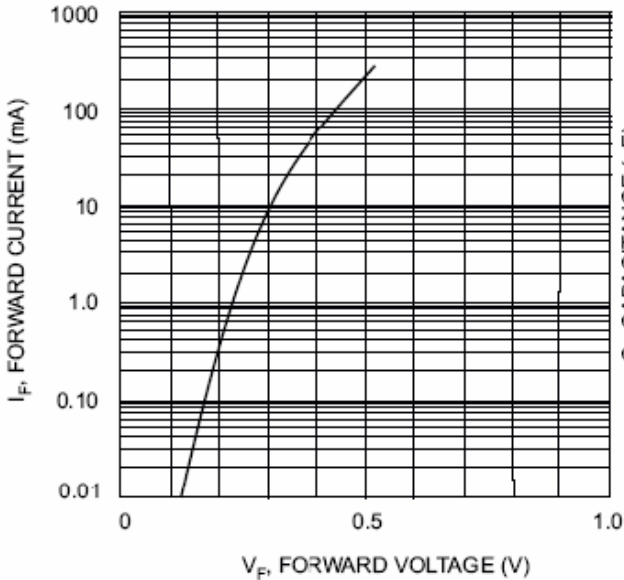


Fig. 1 Typical Forward Characteristics

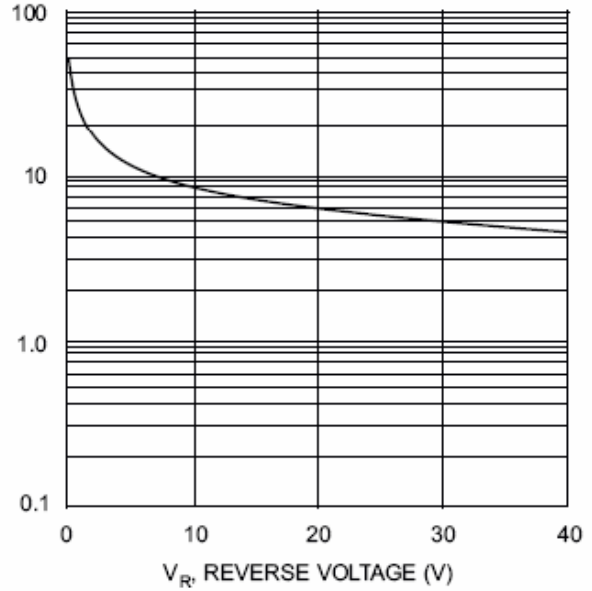


Fig. 2 Typ. Junction Capacitance vs Reverse Voltage